

# **DATASHEET**

## ITR8307/L24/F43

#### **Features**

- Thin
- Fast response time
- High sensitivity
- Pb free
- High analytic
- Compact

## **Description**

The ITR8307/L24/F43 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black

thermoplastic housing The phototransistor receives radiation from the IR only .This is the normal situation. But when an object is in between, phototransistor could not receive the radiation.

### **Applications**

- Various microcomputer control equipment
- Floppy disk driver
- Cassette type recorder
- Camera
- VCR

#### **Device Selection Guide**



Device No.	Chip Material	LENS COLOR		
IR	GaAs	Water Clear		
PT	Silicon	Water Clear		

## **Absolute Maximum Ratings (Ta=25℃)**

	Parameter	Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	$V_R$	6	V
	Forward Current	$I_{\mathrm{F}}$	50	mA
	Peak Forward Current (*1) Pulse width ≤100µ s, Duty cycle=1%	${ m I_{FP}}$	1	A
Output	Collector Power Dissipation	$P_{\rm C}$	100	mW
	Collector Current	$I_{\mathrm{C}}$	20	mA
	Collector-Emitter Voltage	$B V_{CEO}$	35	V
	Emitter-Collector Voltage	$B V_{ECO}$	6	V
Operating Temperature		Topr	-25~+85	$^{\circ}$ C
Storage Temperature		Tstg	-30~+90	°C
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	$^{\circ}\!\mathbb{C}$

(\*1)  $tw=100 \mu sec.$ , T=10 msec. (\*2) t=5 Sec

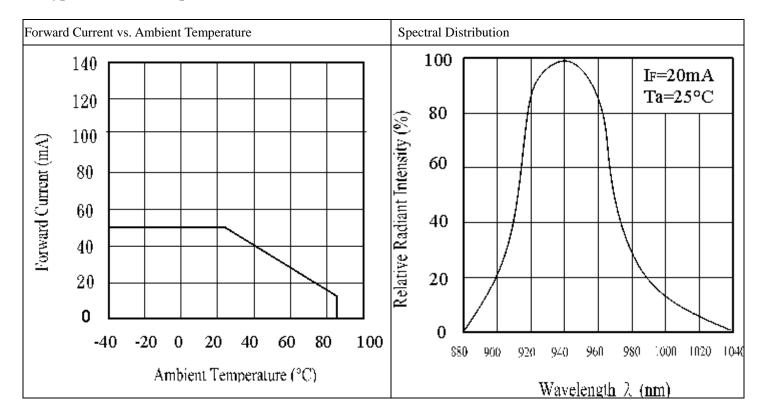


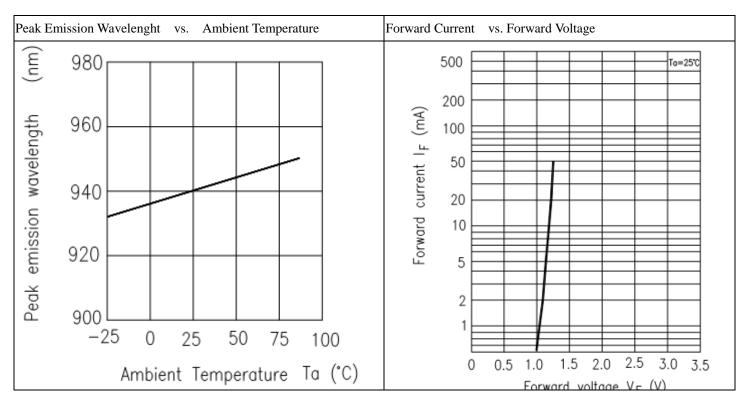
# **Electro-Optical Characteristics (Ta=25°C)**

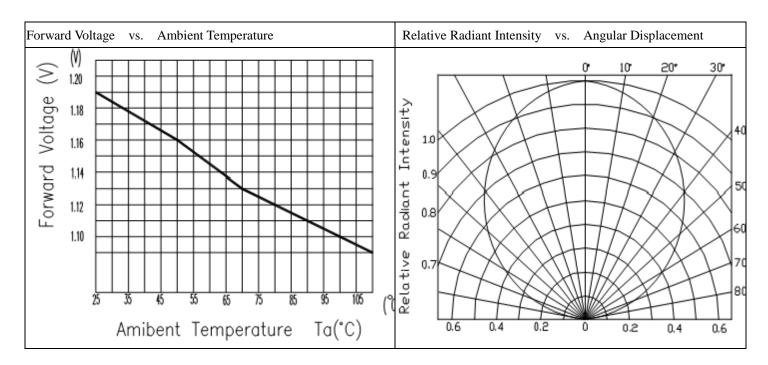
Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input	Forward Voltage	$V_{\mathrm{F}}$		1.2	1.4	V	I <sub>F</sub> =20mA	
	Reverse Current	$I_R$			10	μΑ	V <sub>R</sub> =5V	
	Peak Wavelength	λ <sub>P</sub>		940		nm	I <sub>F</sub> =20mA	
Output	Dark Current	$I_{CEO}$			1	μΑ	$V_{\text{CE}}$ =10V, Ee=1mW/cm <sup>2</sup>	
Transfer Characteristics	Collect Current	I <sub>C</sub> (ON)	0.5			mA	V <sub>CE</sub> =5V I <sub>F</sub> =20mA	
	Leakage Current	ILEAK			5	μΑ	V <sub>CE</sub> =2V I <sub>F</sub> =4mA	
	Rise time	t <sub>r</sub>		80	400	μs	$V_{\text{CE}}$ =2V $I_{\text{C}}$ =10mA	
	Fall time	$t_{\mathrm{f}}$		70	400	μs	$R_{L}=100\Omega$ $d=1mm$	



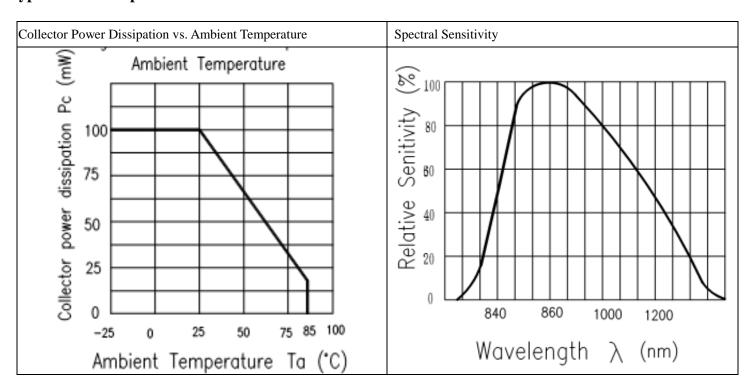
### Typical Electrical/Optical/Characteristics Curves for IR

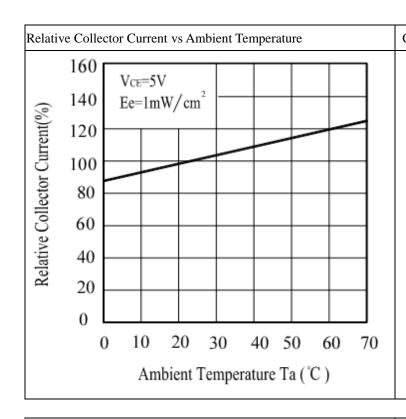


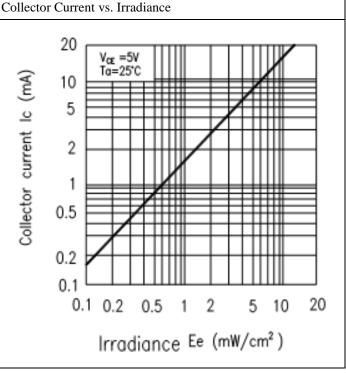


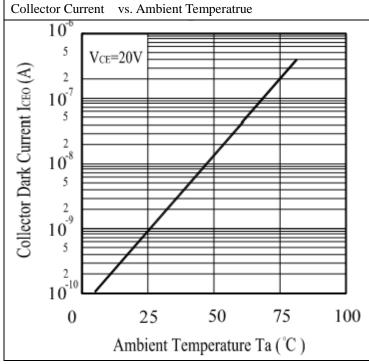


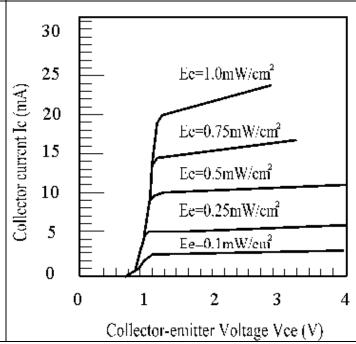
## Typical Electro/Optical/Characteristics Curves for PT







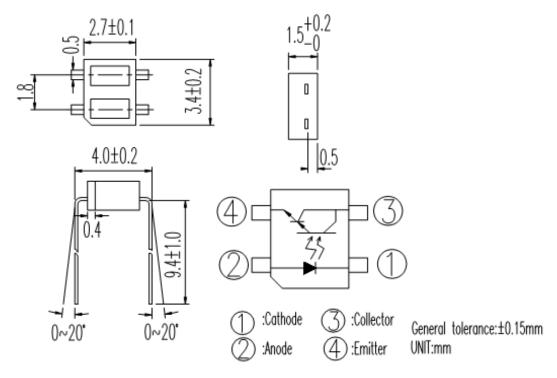




Collector Current vs. Collector-emitter Voltage



## **Package Dimension**



Notes: 1.All dimensions are in millimeters

2.Tolerances unless dimensions ±0.25mm



#### **Packing Quantity Specification**

- 1. 1000pcs/1Bag
- 2. 1Bag/1Carton

#### **Label Form Specification**



- CPN: Customer's Product Number
- P/N: Product Number
- QTY: Packing Quantity
- CAT: Luminous Intensity Rank
- HUE: Dom. Wavelength Rank
- REF: Forward Voltage Rank
- LOT No: Lot Number
- X: Month
- Reference: Identify Label Number

#### Notes

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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ITR8307/L24/F43